

Technical Data Green Products

Data Sheet N1157, Rev. -

Power Surface Mount Schottky Rectifier (60V, 120Amp)

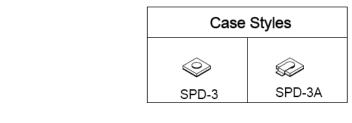
Applications:

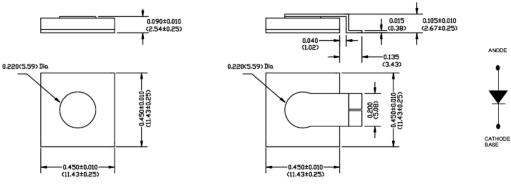
- · Switching power supply
- Converters
- Reverse battery protection
- Redundant power subsystems
- Many other high current AC/DC power supplies

Features:

- 150 °C T_J operation
- Low forward voltage drop
- Low reverse leakage current
- High surge capacities
- High frequency operation
- · Guaranteed reverse avalanche capability
- Low profile surface mount package
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- · Additional testing can be offered upon request

Mechanical Dimensions: In Inches / mm





SPD-3A SPD-3A

Suffix "R" Denotes Reversed Polarity

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Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	60	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form	120	А
Max. Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	1650	А
Non-Repetitive Avalanche Energy(per leg)	E _{AS}	T_J =25 $^{\circ}$ C, I_{AS} =2.9A, L=6.5mH	27.3	mJ
Repetitive Avalanche Current(per leg)	I _{AR}	I_{AS} decaying linearly to 0 in 1 μ sec Frequency limited by T_J max. $V_A{=}1.5{\times}V_R$	2.9	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop*	V_{F1}	@ 120A, Pulse, T _J = 25 °C	0.60	V
	V_{F2}	@ 120A, Pulse, T _J = 125 °C	0.57	V
Max. Reverse Current (per	I _{R1}	$@V_R = \text{rated } V_R$, Pulse,	11	mA
leg) *		T _J = 25 °C		
	I_{R2}	$@V_R = rated V_R$, Pulse,	840	mΑ
		T _J = 125 °C		
Max. Junction Capacitance	CJ	@V _R = 5V, T _C = 25 °C	4800	pF
(per leg)		$f_{SIG} = 1MHz$, $V_{SIG} = 50mV(p-p)$		

^{*} Pulse Width < 300 μ s, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	°C
Max. Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.20	°C/W
Case Style		SPD-3/A		

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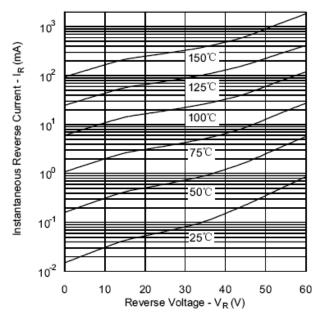
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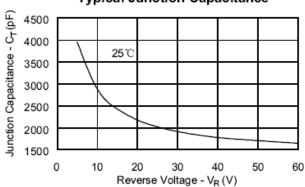
Typical Forward Characteristics 10² 10¹ 10¹ 10² 25°C 10² 10³ 0.0 0.2 0.4 0.6 0.8

Forward Voltage Drop - VF(V)

Typical Reverse Characteristics



Typical Junction Capacitance



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